

# Phase Control Thyristors (Hockey PUK Version), 1650 A



PRODUCT SUMMARY					
Package	A-24 (K-PUK)				
Diode variation	Single SCR				
I <sub>T(AV)</sub>	1650 A				
$V_{DRM}/V_{RRM}$	1200 V, 1400 V, 1600 V, 1800 V, 2000 V				
$V_{TM}$	1.73 V				
I <sub>GT</sub>	100 mA				
TJ	-40 °C to 125 °C				

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

## Pb-free RoHS

## ROHS

#### TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS VALUES		UNITS				
1		1650	A				
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C				
1		3080	A				
IT(RMS)	T <sub>hs</sub>	25	°C				
l	50 Hz	30 500	A				
I <sub>TSM</sub>	60 Hz	32 000					
l <sup>2</sup> t	50 Hz	4651	- kA <sup>2</sup> s				
1-1	60 Hz	4250	KA-S				
V <sub>DRM</sub> /V <sub>RRM</sub>		1200 to 2000	V				
tq	Typical	200	μs				
T <sub>J</sub>		-40 to 125	°C				

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA				
	12	1200	1300					
	14	1400	1500					
VS-ST1200CK	16	1600	1700	100				
	18	1800	1900					
	20	2000	2100					



PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current		180° condu	180° conduction, half sine wave double side (single side) cooled		1650 (700)	Α
at heatsink temperature	I <sub>T(AV)</sub>	double side			55 (85)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	3080	
		t = 10 ms	No voltage		30 500	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		32 000	Α
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms 100 % V <sub>RBM</sub>		25 700		
		t = 8.3 ms	reapplied	Sinusoidal half wave.	26 900	
Maximum I <sup>2</sup> t for fusing	t = 8. $t = 10$	t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	4651	kA <sup>2</sup> s
		t = 8.3 ms			4250	
		t = 10 ms			3300	
		t = 8.3 ms	reapplied		3000	
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to	t = 0.1 ms to 10 ms, no voltage reapplied			kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.91	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			v
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.19	1115.2
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 4000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.73	V
Maximum holding current	I <sub>H</sub>	T _ 05 °C	T 05 00 and a red 40 V artist of 1			mA
Typical latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load			1000	IIIA

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs		
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.9			
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/μs, $V_R$ = 50 V, dV/dt = 20 V/μs, gate 0 V 100 $\Omega$ , $t_p$ = 500 μs	200	μs		

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA



TRIGGERING						
DADAMETED	SYMBOL		VALUES		LINUTO	
PARAMETER	STINIBUL		ST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	16		W
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	;	3	] vv
Maximum peak positive gate current	I <sub>GM</sub>			3	.0	Α
Maximum peak positive gate voltage	+ V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms		0	V	
Maximum peak negative gate voltage	- V <sub>GM</sub>		5.0			
DC gate current required to trigger		T <sub>J</sub> = -40 °C	Maximum required gate trigger/ current/voltage are the lowest	200	-	mA
	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		100	200	
		T <sub>J</sub> = 125 °C		50	-	
		T <sub>J</sub> = -40 °C	value which will trigger all units 12 V anode to cathode applied	1.4	-	
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 v anode to camode applied	1.1	3.0	V
		T <sub>J</sub> = 125 °C		0.9	-	
DC gate current not to trigger	I <sub>GD</sub>	T. T. magazinas uma	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	$V_{\mathrm{GD}}$	$T_J = T_J \text{ maximum}$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	°C		
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150			
Maximum thermal resistance, junction to heatsink	D	DC operation single side cooled 0.0.4				
	R <sub>thJ-hs</sub>	DC operation double side cooled	0.021	K/W		
Maximum thermal resistance,	Б	DC operation single side cooled	0.006	<b>I</b> √VV		
case to heatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.003			
Mounting force, ± 10 %			24 500 (2500)	N (kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet	A-24 (ł	(-PUK)		

△R <sub>thJC</sub> CONDUCTION								
CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR	RCONDUCTION	TEST CONDITIONS	UNITS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS		
180°	0.003	0.003	0.002	0.002				
120°	0.004	0.004	0.004	0.004				
90°	0.005	0.005	0.005	0.005	$T_J = T_J$ maximum	K/W		
60°	0.007	0.007	0.007	0.007				
30°	0.012	0.012	0.012	0.012				

#### Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

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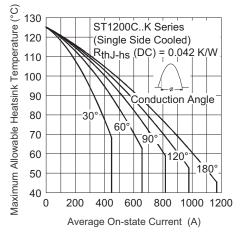


Fig. 1 - Current Ratings Characteristics

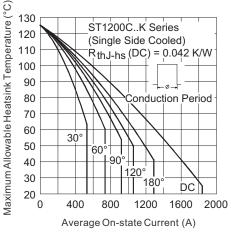


Fig. 2 - Current Ratings Characteristics

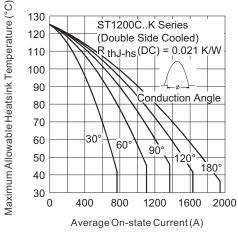


Fig. 3 - Current Ratings Characteristics

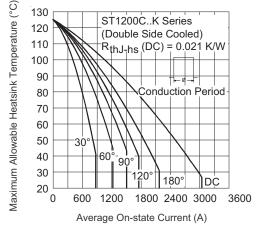


Fig. 4 - Current Ratings Characteristics

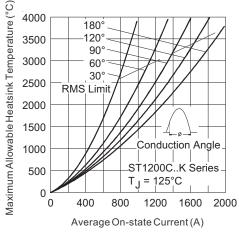


Fig. 5 - On-State Power Loss Characteristics

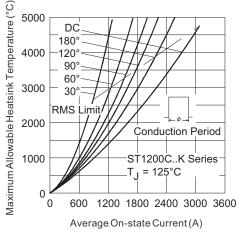
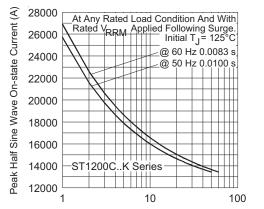


Fig. 6 - On-State Power Loss Characteristics



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Number Of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

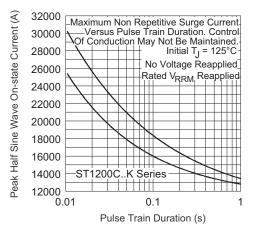


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

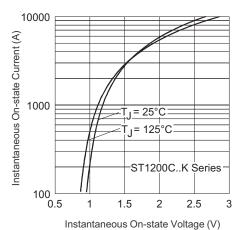


Fig. 9 - On-State Voltage Drop Characteristics

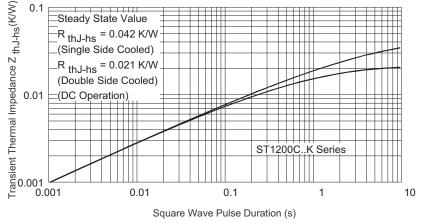


Fig. 10 - Thermal Impedance Z<sub>thJ-hs</sub> Characteristics

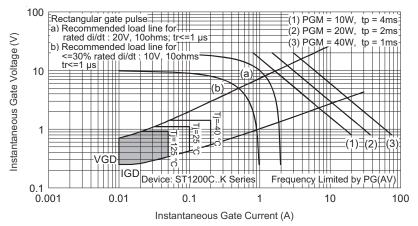
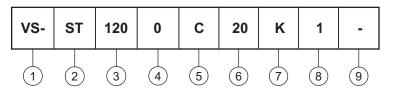


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = Converter grade

5 - C = Ceramic PUK

6 - Voltage code: Code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

**7** - K = PUK case A-24 (K-PUK)

8 - 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

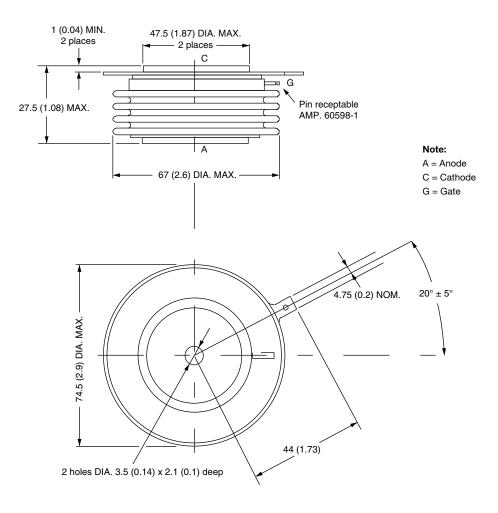
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95081		



## K-PUK (A-24)

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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